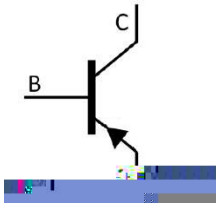
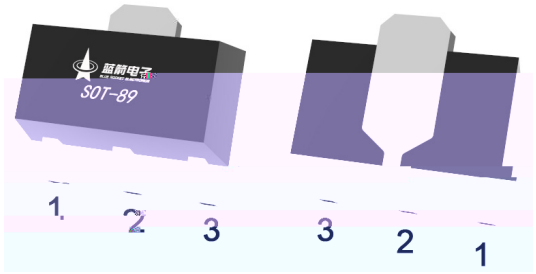
SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

600mA

Collector currents to 600mA, HF Product.

General purpose amplifier.



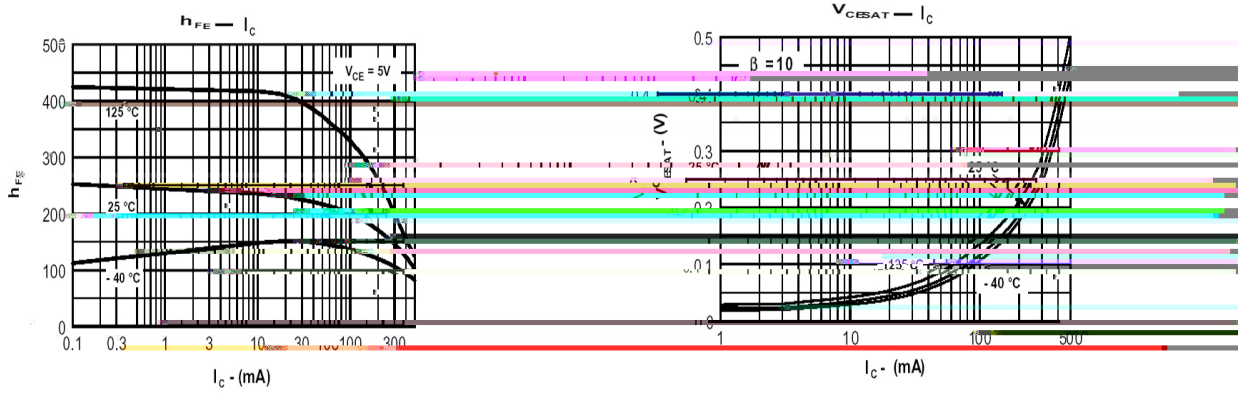


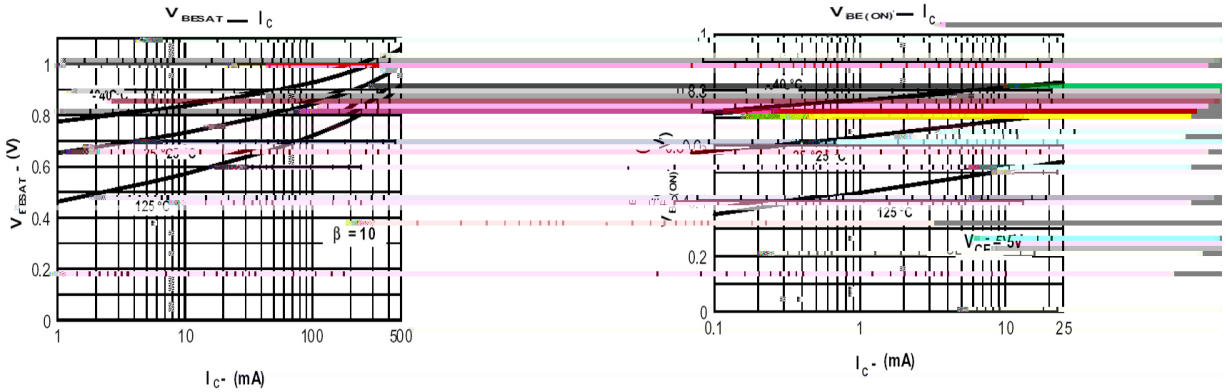
PIN1 Base PIN 2 Collector PIN 3 Emitter

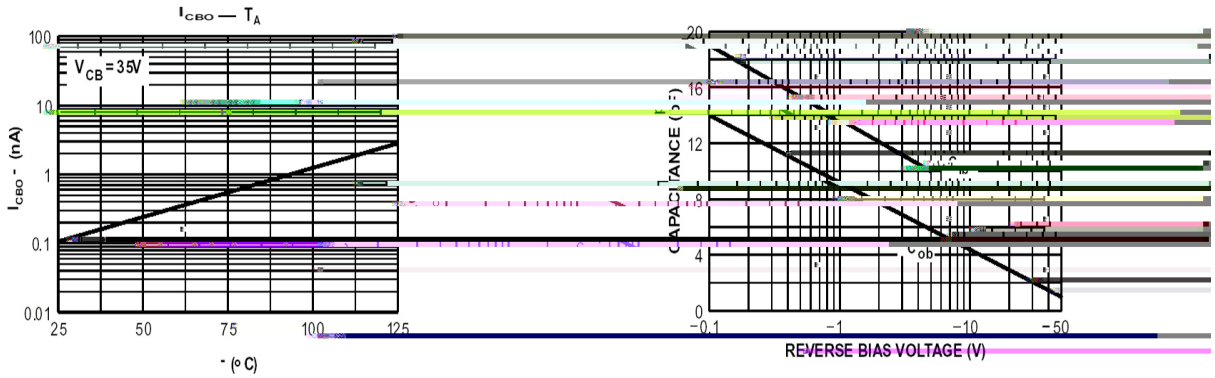
Marking	H2F ⁑

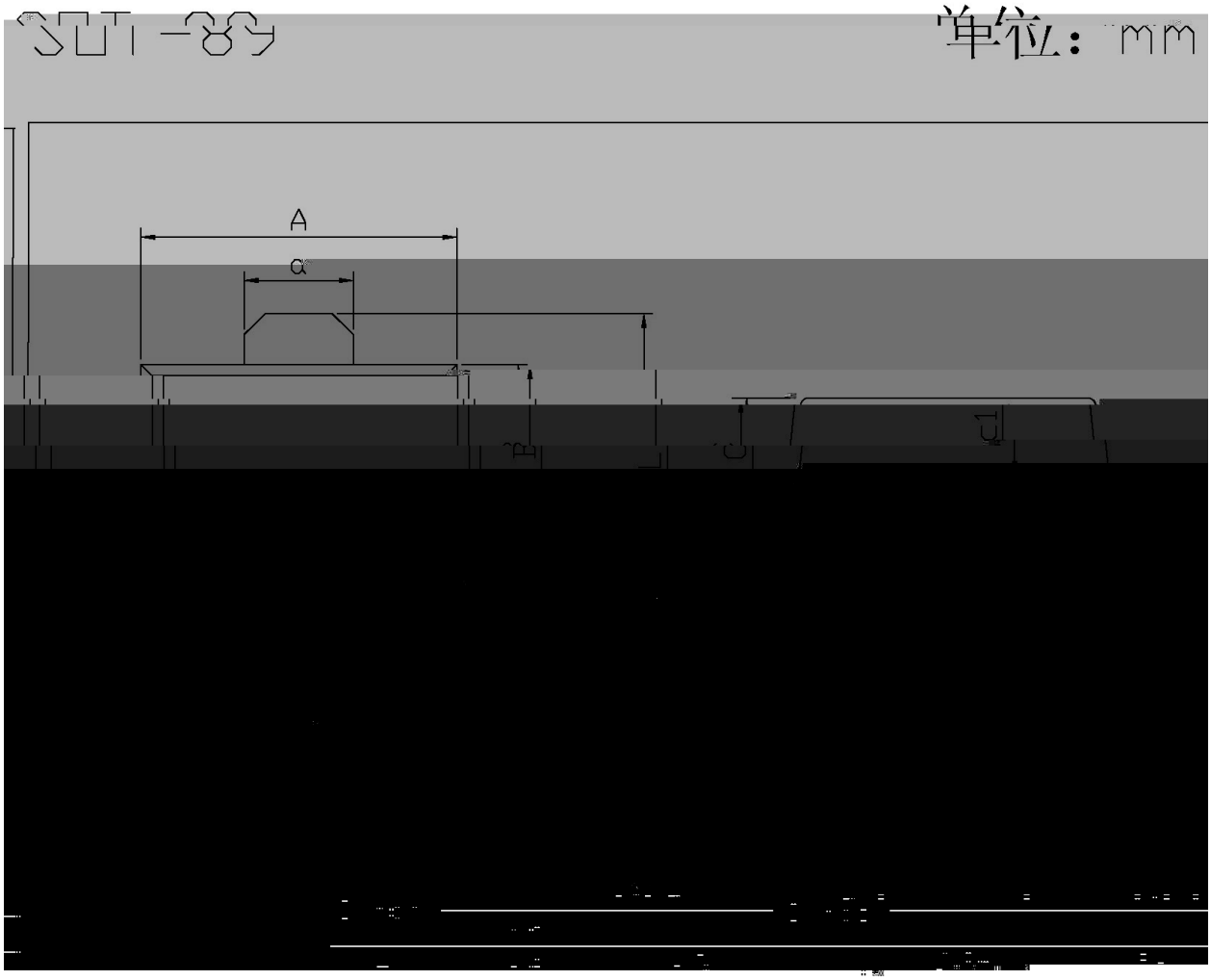
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

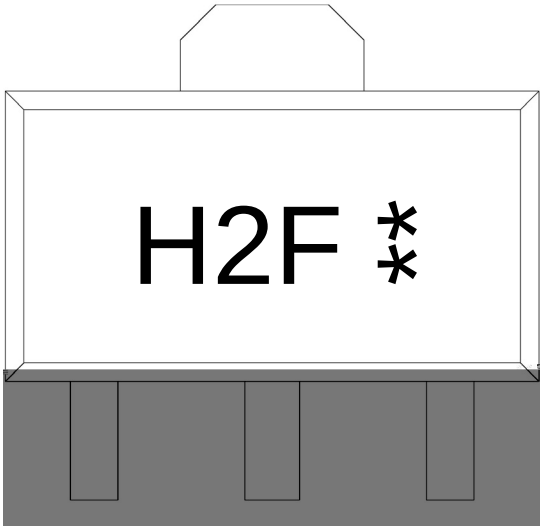
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
CollectorOutput Capacita0						
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10μA I_E=0	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-10μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-50V I_E=0			-0.01	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-10V I_C=-150mA*	100		300	
	$h_{FE(2)}$	V_{CE}=-10V I_C=-500mA*	50			
	$h_{FE(3)}$	V_{CE}=-10V I_C=-10mA	100			
	$h_{FE(4)}$	V_{CE}=-10V I_C=-1.0mA	100			
	$h_{FE(5)}$	V_{CE}=-10V I_C=-0.1mA	75			
Collector to Emitter Saturation Voltage	$V_{CE(sat)\ (1)}$	I_C=-150mA I_B=-15mA			-0.4	V
	$V_{CE(sat)\ (2)}$	I_C=-500mA I_B=-50mA			-1.6	V
Emitter to Base Saturation Voltage	$V_{BE(sat)\ (1)}$	I_C=-150mA I_B=-15mA			-1.3	V
	$V_{BE(sat)\ (2)}$	I_C=-500mA I_B=-50mA			-2.6	V
Transition Frequency	f_T	V_{CE}=-20V I_C=-50mA f=100MHz	200			MHz
a=20C5haracte0T						


h FE — I C
V CE = 5V
125 °C
25 °C
- 40 °C
h FE
I C - (mA)
V CESAT — I C
β = 10
V CESAT - (V)
- 40 °C
I C - (mA)


V BESAT — I C
- 40 °C
25 °C
125 °C
β = 10
V FBSAT - (V)
I C - (mA)
V BE(ON) — I C
- 40 °C
25 °C
125 °C
V CE = 5v
V BE(ON) - (V)
I C - (mA)


I CBO — T A
V CB = 35V
I CBO - (nA)
- (o C)
CAPACITANCE (pF)
Cob
REVERSE BIAS VOLTAGE (V)


SOT-89
单位：mm
A
C



H

2F

**

Note:

H:	Company Code
2F:	Product Type Code
**:	Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)

			Note:
1	150 180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type	Units	Dimension	(unit mm³)